

MBM500E33E2

Silicon N-channel IGBT 3300V E2 version

FEATURES

- * Soft switching behavior & low conduction loss:
Soft low-injection punch-through High conductivity IGBT.
- * Low driving power due to low input capacitance MOS gate.
- * Low noise recovery: Ultra soft fast recovery diode.
- * High thermal fatigue durability:
($\Delta T_c=70K$, $N>30,000$ cycles)
AlSiC base-plate/AlN substrate

ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ C$)

Item	Symbol	Unit	MBM500E33E2
Collector Emitter Voltage	V_{CES}	V	3,300
Gate Emitter Voltage	V_{GES}	V	± 20
Collector Current	DC	I_C	500 ($T_c=95^\circ C$)
	1ms	I_{CP}	1,000
Forward Current	DC	I_F	500
	1ms	I_{FM}	1,000
Operating Junction Temperature	$T_{vj,op}$	$^\circ C$	-40 ~ +150
Maximum Junction Temperature	$T_{vj,max}$	$^\circ C$	175 (4)
Storage Temperature	T_{stg}	$^\circ C$	-50 ~ +125
Isolation Voltage	V_{ISO}	V_{RMS}	6,000(AC 1 minute)
Screw Torque	Terminals (M4/M8)	-	2/15 (1)
	Mounting (M6)	-	6 (2)

Notes: (1) Recommended Value $1.8 \pm 0.2/15^{+0}_{-3} N \cdot m$ (2) Recommended Value $5.5 \pm 0.5 N \cdot m$
(4) Only static operation is applicable. Please refer to LD-ES-130737.

ELECTRICAL CHARACTERISTICS

Item	Symbol	Unit	Min.	Typ.	Max.	Test Conditions
Collector Emitter Cut-Off Current	I_{CES}	mA	-	-	4	$V_{CE}=3,300V, V_{GE}=0V, T_j=25^\circ C$
			-	7	20	$V_{CE}=3,300V, V_{GE}=0V, T_j=125^\circ C$
Gate Emitter Leakage Current	I_{GES}	nA	-500	-	+500	$V_{GE}=\pm 20V, V_{CE}=0V, T_j=25^\circ C$
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	V	2.5	2.95	3.5	$I_C=500A, V_{GE}=15V, T_j=125^\circ C$
			-	3.1	-	$I_C=500A, V_{GE}=15V, T_j=150^\circ C$
Gate Emitter Threshold Voltage	$V_{GE(TO)}$	V	5.5	6.5	7.5	$V_{CE}=10V, I_C=500mA, T_j=25^\circ C$
Input Capacitance	C_{ies}	nF	-	65	-	$V_{CE}=10V, V_{GE}=0V, f=100kHz, T_j=25^\circ C$
Internal Gate Resistance	R_{ge}	Ω	-	2.1	-	$V_{CE}=10V, V_{GE}=0V, f=100kHz, T_j=25^\circ C$
Switching Times	Rise Time	t_r	1.1	1.6	2.1	$V_{CC}=1,650V, I_C=500A$
	Turn On Time	t_{on}	1.2	2.2	2.6	$L_s=150nH$
	Fall Time	t_f	0.9	1.7	2.6	$R_G=8.2\Omega/8.2\Omega$ (3)
	Turn Off Time	t_{off}	2.1	3.8	4.9	$V_{GE}=\pm 15V, T_j=125^\circ C$
Peak Forward Voltage Drop	V_{FM}	V	2.2	2.5	3.0	$I_F=500A, V_{GE}=0V, T_j=125^\circ C$
			-	2.5	-	$I_F=500A, V_{GE}=0V, T_j=150^\circ C$
Reverse Recovery Time	t_{rr}	μs	-	0.55	0.82	$V_{CC}=1,650V, I_F=500A, L_s=150nH$ $T_j=125^\circ C$
Turn On Loss	$E_{on(10\%)}$	J/P	-	0.68	0.95	$T_j=125^\circ C$
	$E_{on(full)}$		-	0.75	-	$T_j=150^\circ C$
Turn Off Loss	$E_{off(10\%)}$	J/P	-	0.83	-	$T_j=125^\circ C$
	$E_{off(full)}$		-	0.72	0.86	$T_j=150^\circ C$
Reverse Recovery Loss	$E_{rr(10\%)}$	J/P	-	0.79	-	$T_j=125^\circ C$
			-	0.82	-	$T_j=150^\circ C$
	$E_{rr(full)}$	J/P	-	0.61	0.80	$T_j=125^\circ C$
			-	0.72	-	$T_j=150^\circ C$

Notes:(3) R_G and C_{GE} value are the test condition's value for evaluation of the switching times, not recommended value.

Please, determine the suitable R_G value after the measurement of switching waveforms(overshoot voltage, etc.) with appliance mounted.

- * Please contact our representatives at order.
- * For improvement, specifications are subject to change without notice.
- * For actual application, please confirm this spec sheet is the newest revision.

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THERMAL CHARACTERISTICS

Item		Symbol	Unit	Min.	Typ.	Max.	Test Conditions
Thermal Impedance	IGBT	Rth(j-c)	K/W	-	-	0.024	Junction to case
	FWD	Rth(j-c)		-	-	0.049	
Contact Thermal Impedance		Rth(c-f)	K/W	-	0.008	-	Case to fin ($\lambda_{grease}=1W/(m \cdot K)$, heat-sink flatness $\leq 50\mu m$)

MODULE MECHANICAL CHARACTERISTICS

Item		Unit	Characteristics	Conditions
Weight		g	900	
Creepage Distance	Between terminal	mm	>34	E2aux-C2aux
	Terminal-Base	mm	>32	Base-E1aux
Clearance Distance	Between terminal	mm	>19	C1main-E1aux
	Terminal-Base	mm	>28	Base-E1aux
Stray inductance in module		nH	36	Collector-main to Emitter-main
Comparative Tracking Index (CTI)			600	
Module base plate Material			Al-SiC	
Baseplate Thickness		mm	5	
Insulation plate Material			Al N	
Terminal Surface treatment			Ni plating	
Case Material			Poly-Phenilene Sulfide	
Fire and Smoke Category			I2 / F3	NFF 16-102

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DEFINITION OF TEST CIRCUIT

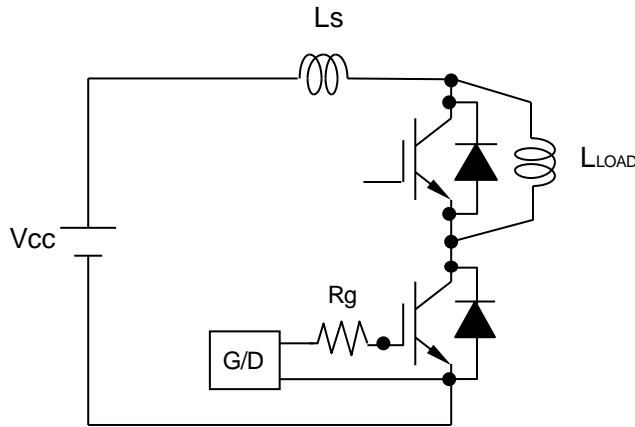


Fig.1 Switching test circuit

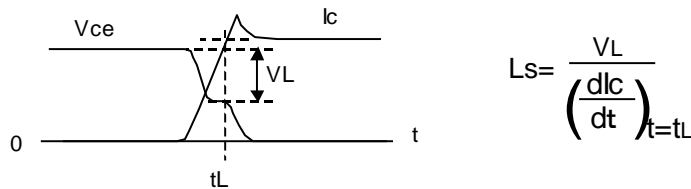


Fig.2 Definition of stray inductance

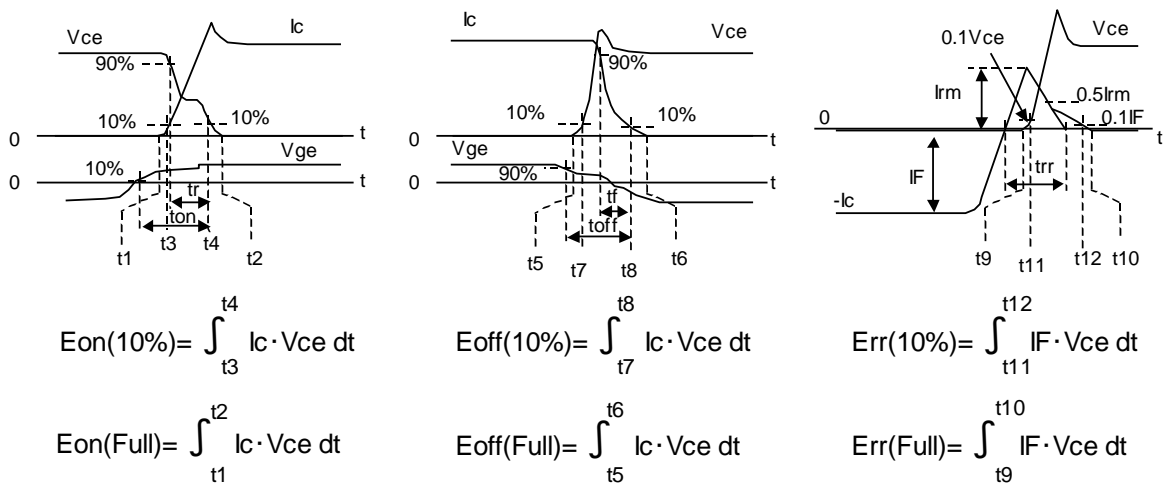
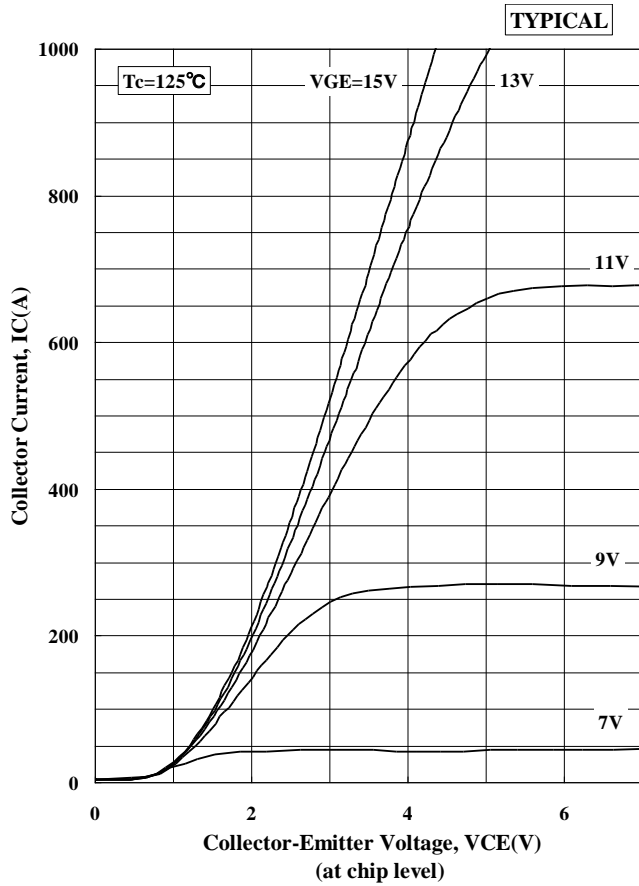


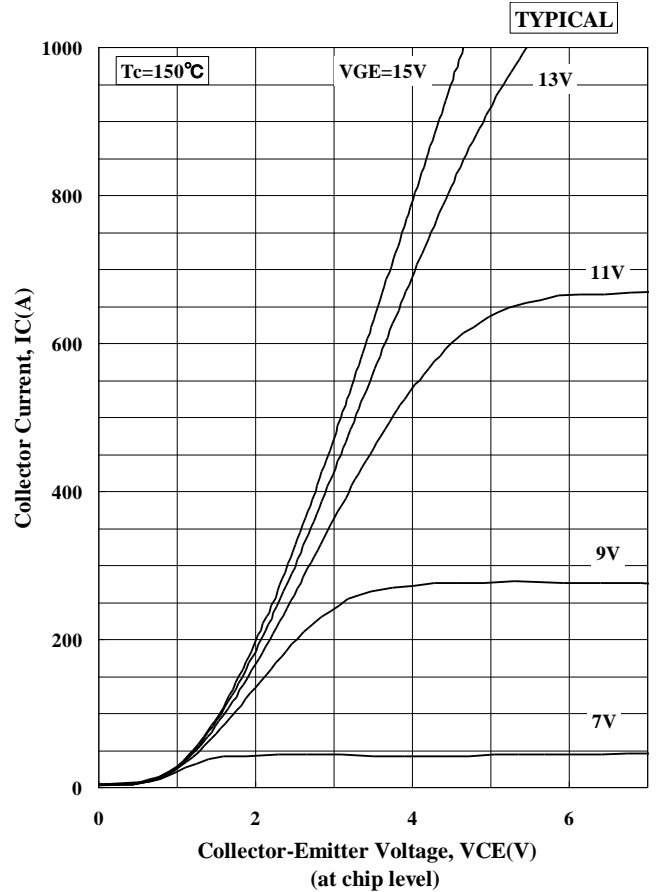
Fig.3 Definition of switching loss

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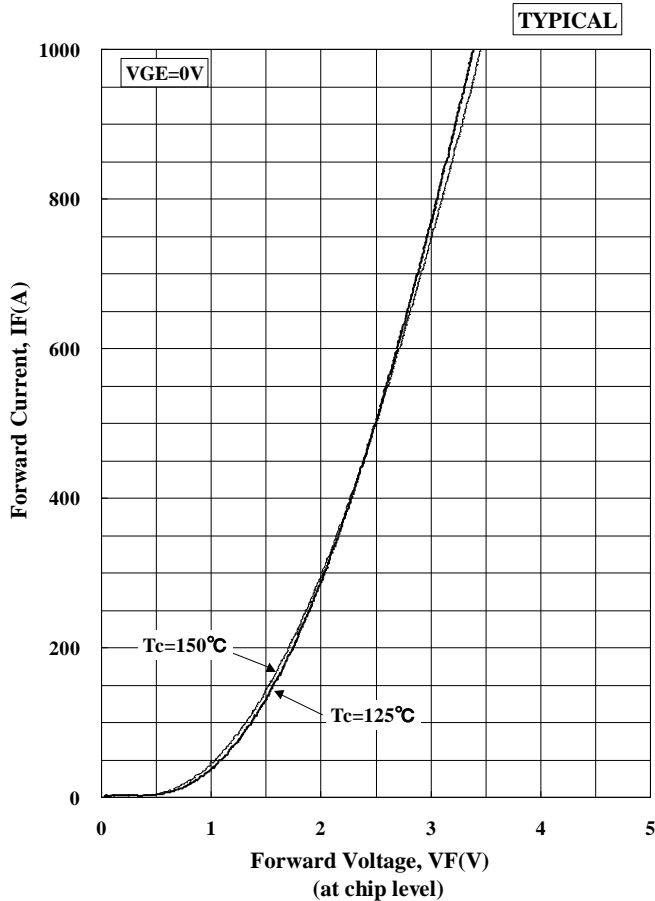
STATIC CHARACTERISTICS



Collector Current vs. Collector to Emitter Voltage



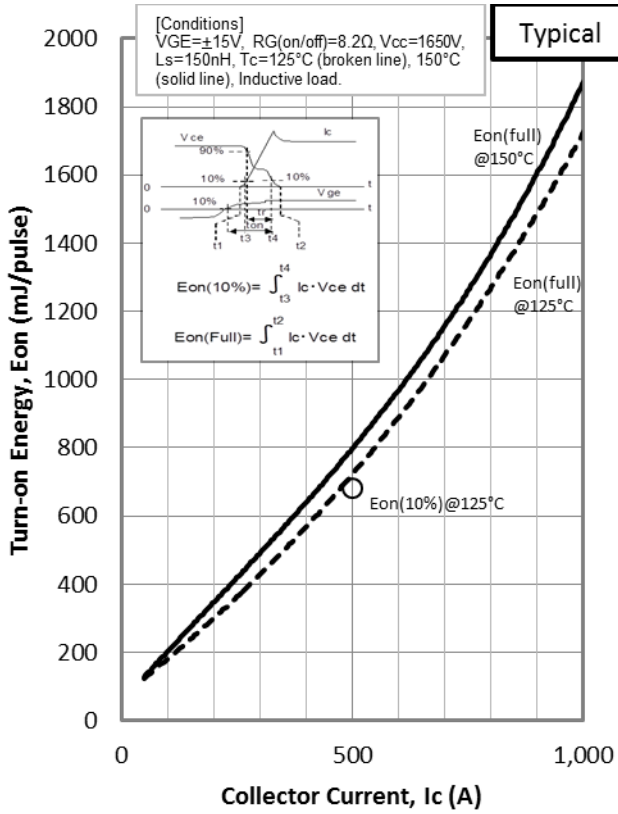
Collector Current vs. Collector to Emitter Voltage



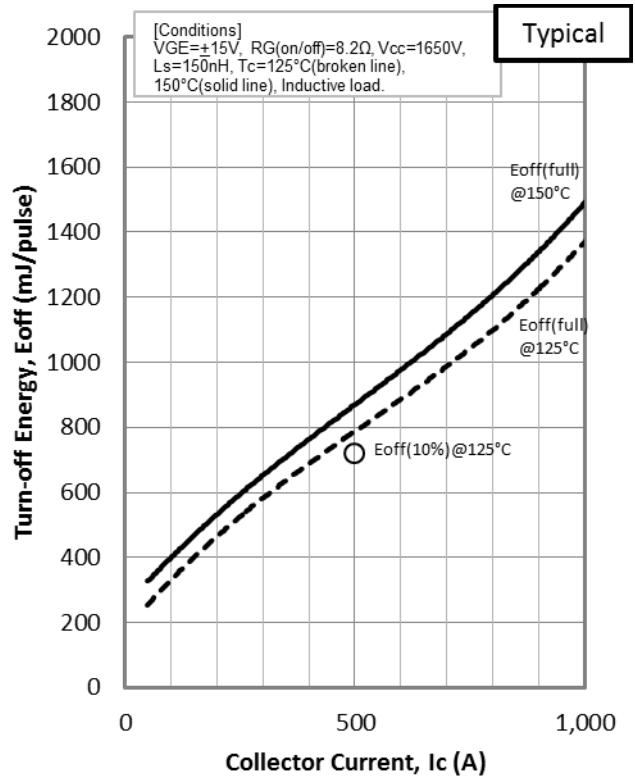
Forward Voltage of free-wheeling diode

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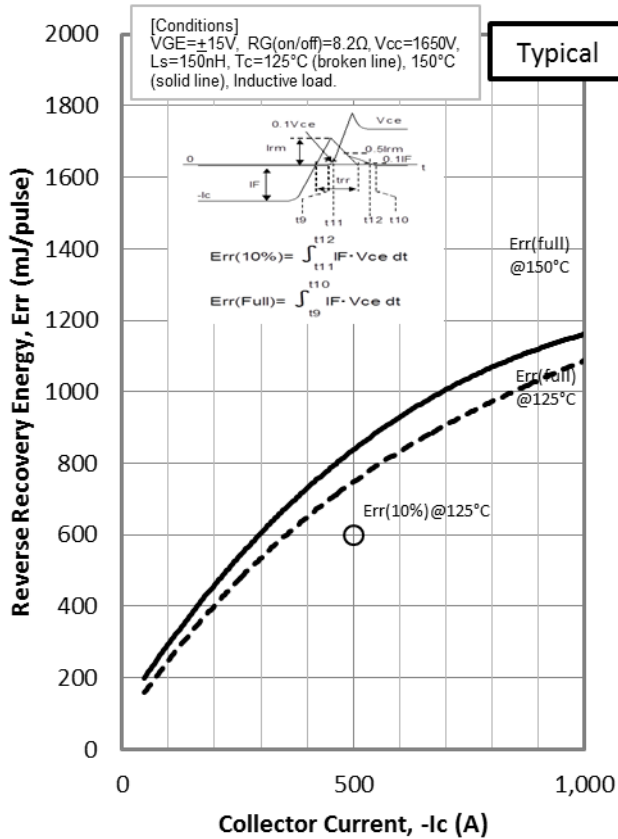
DYNAMIC CHARACTERISTICS



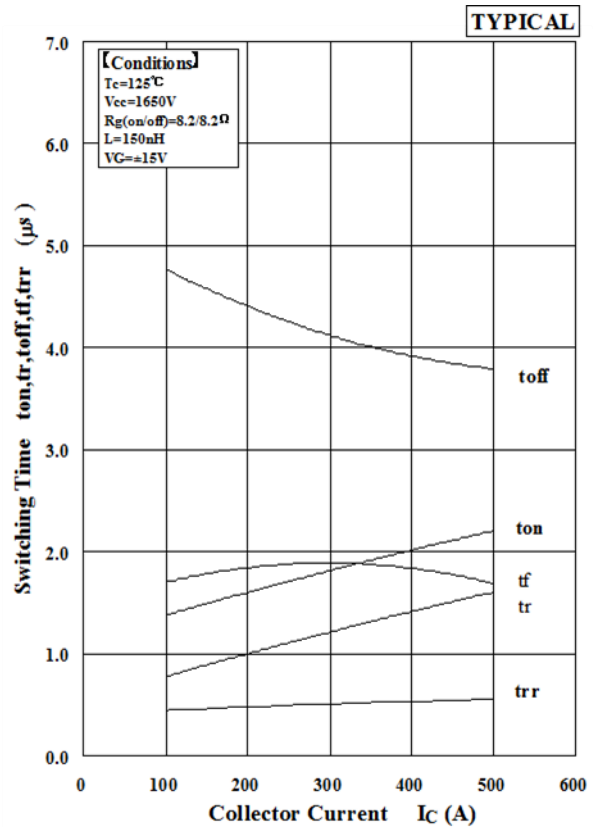
Turn-on energy v.s. Collector current



Turn-off energy v.s. Collector current

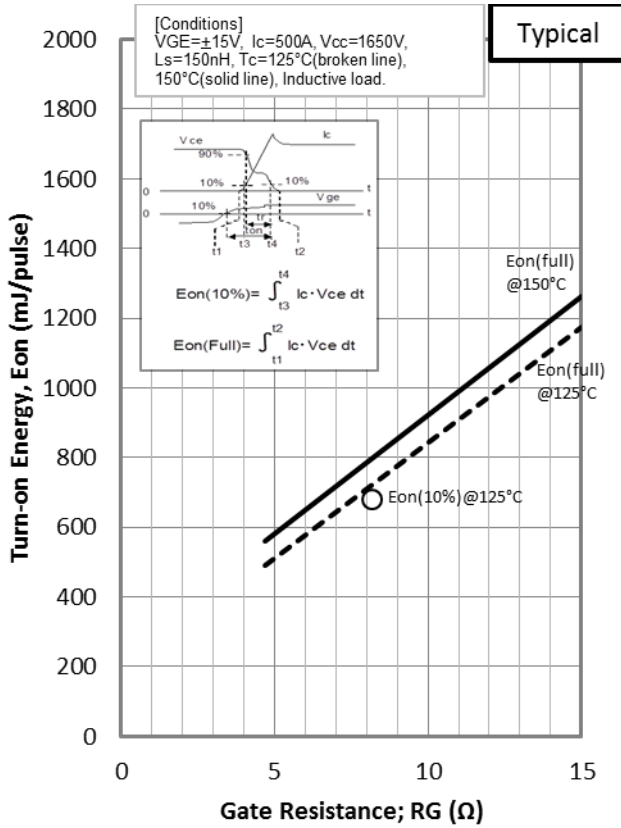


Reverse recovery energy v.s. Collector current

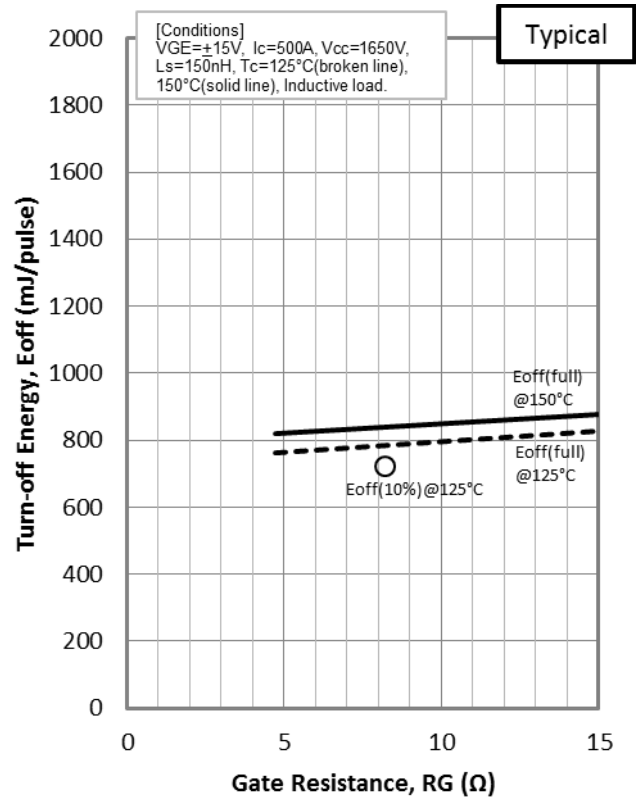


Switching Time vs. Collector Current

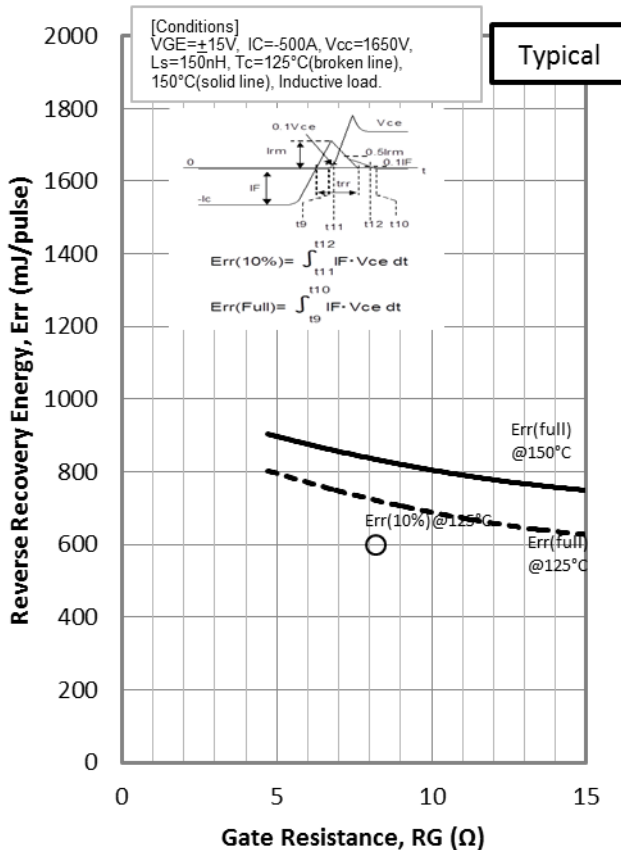
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Turn-on energy v.s. Collector current



Turn-off energy v.s. Gate resistance

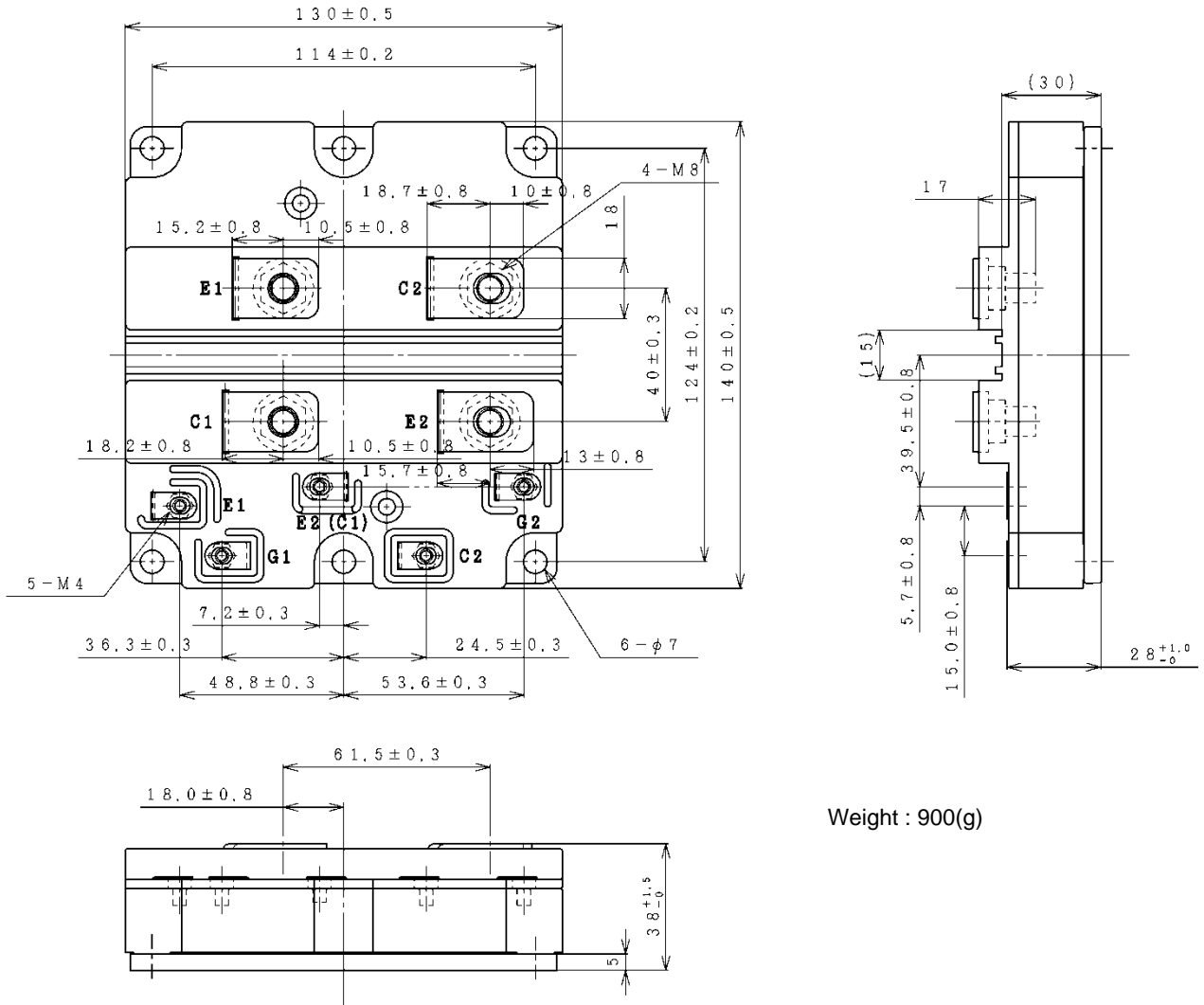


Reverse recovery energy v.s. Gate Resistance

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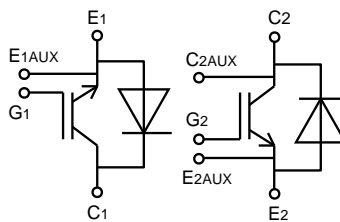
OUTLINE DRAWINGS

Unit in mm



Weight : 900(g)

CIRCUIT DIAGRAM



Material declaration

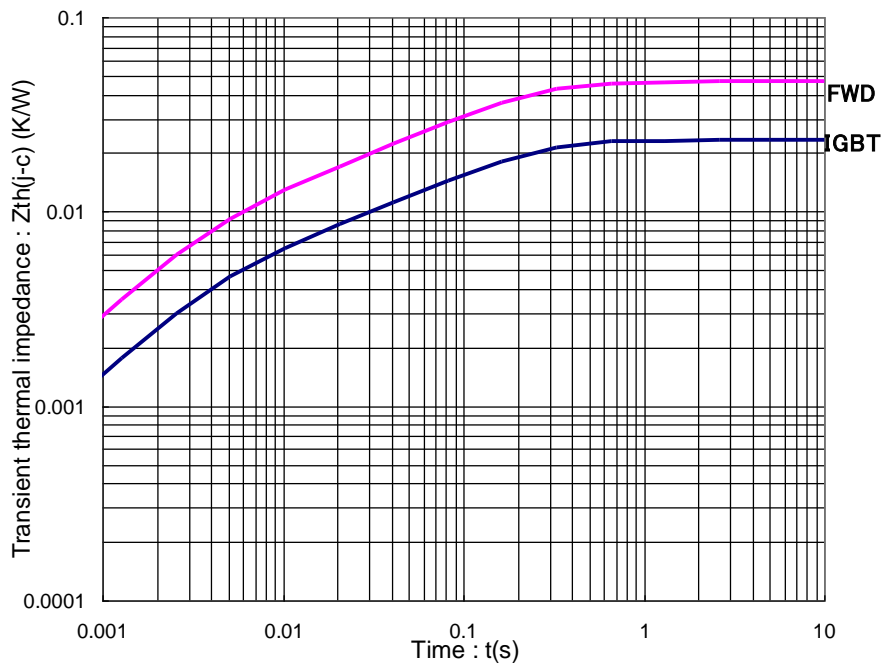
Please note the following materials are contained in the product, in order to keep characteristic and reliability level.

Material	Contained part
Lead (Pb) and its compounds	Solder

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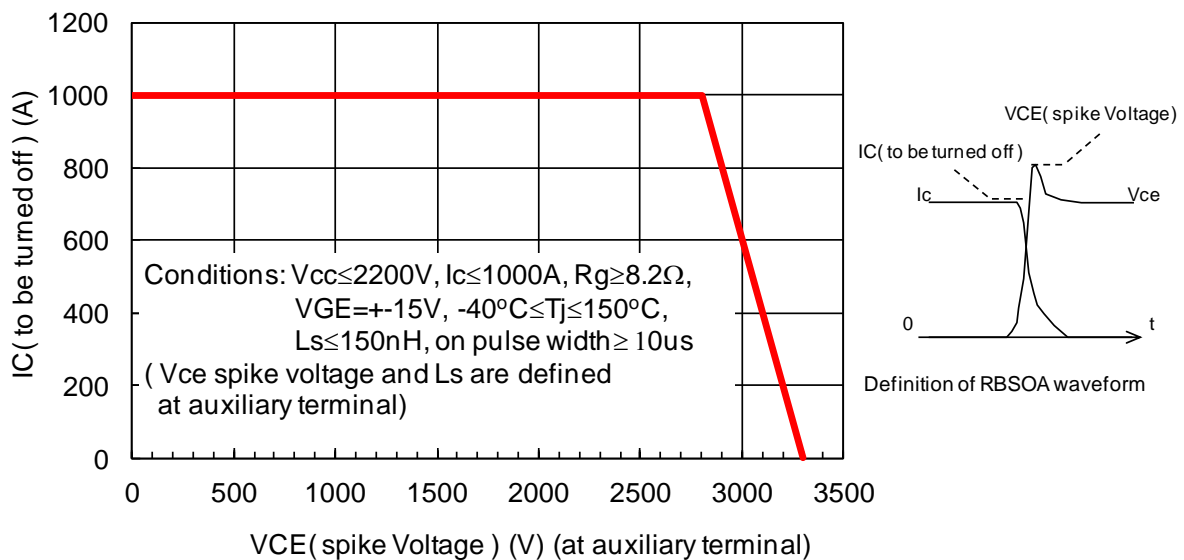
TRANSIENT THERMAL IMPEDANCE

Maximum



Transient Thermal Impedance Curve

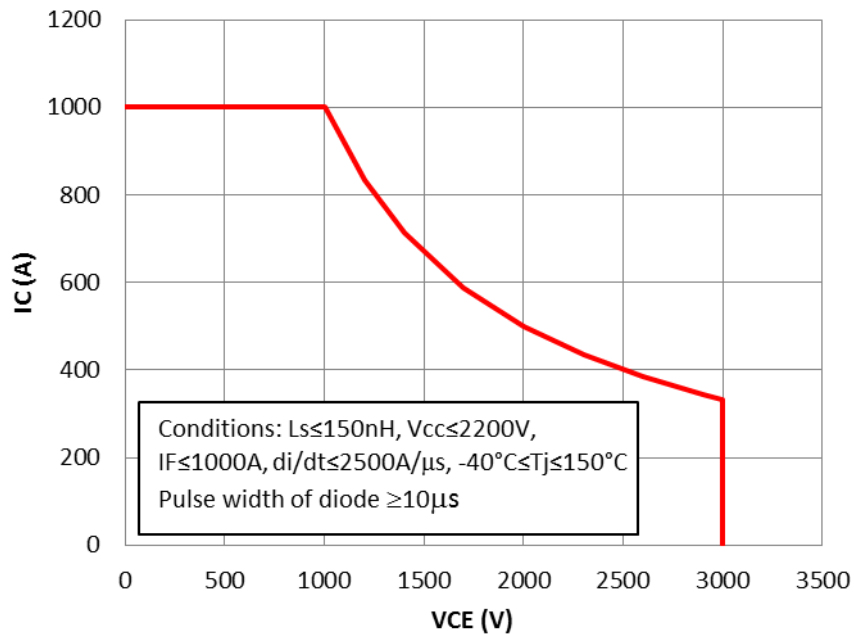
RBSOA



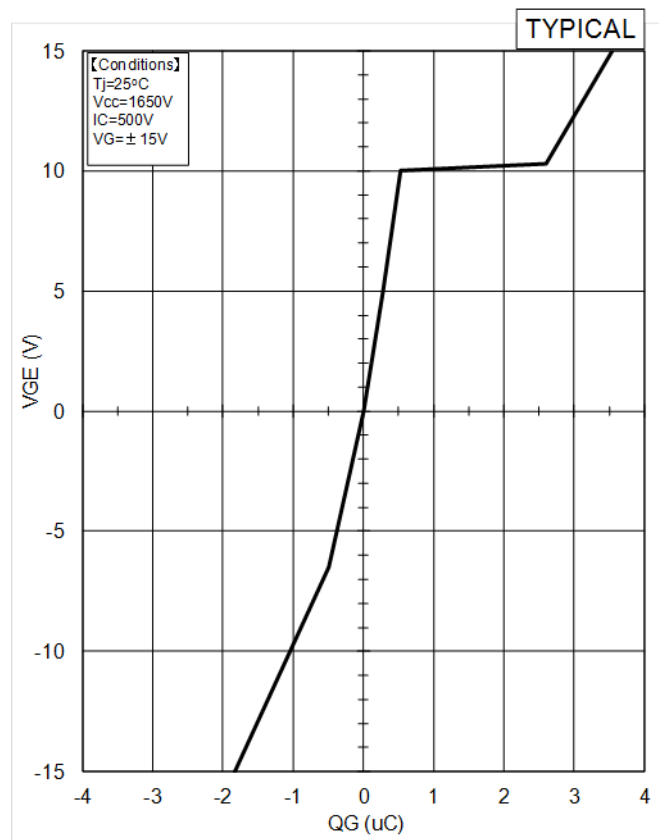
Reverse bias safe operation area (RBSOA)

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RecSOA



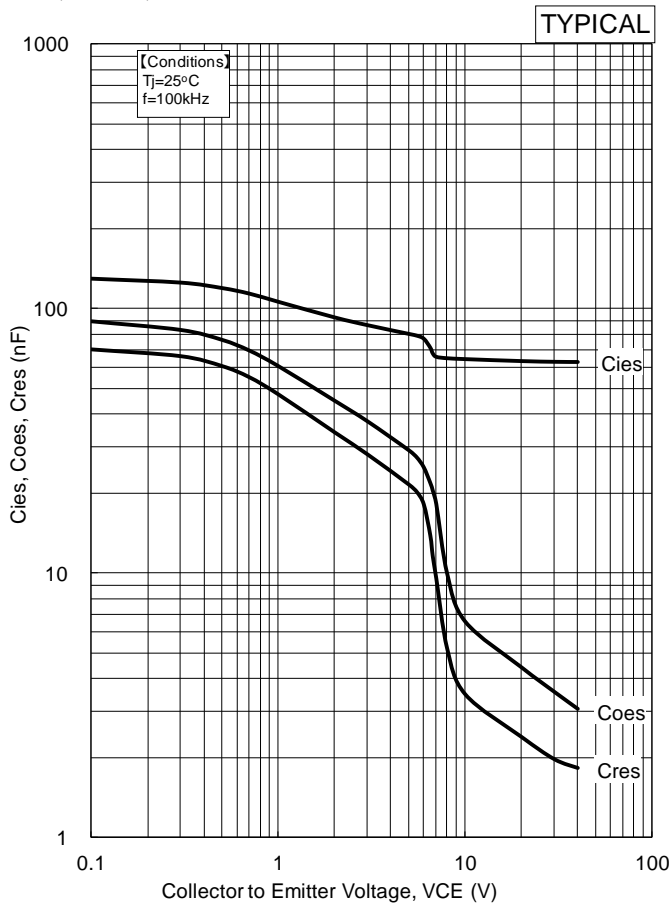
QG-VG Curve



QG-VGE curve

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Cies, Coes, Cres curve



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HITACHI POWER SEMICONDUCTORS

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